

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2N5466 2N5467

DESCRIPTION

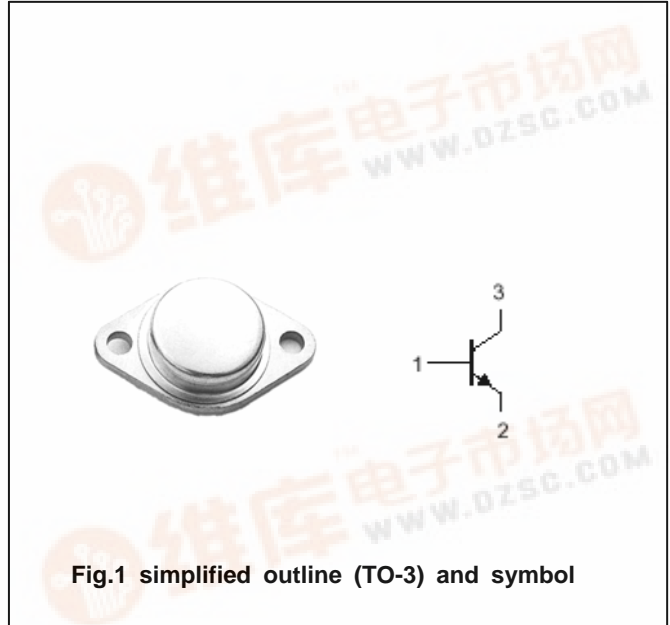
- With TO-3 package
- High-voltage capability
- Fast switching speeds
- Low collector saturation voltage

APPLICATIONS

- They are intended for use in off-line power supplies ,inverter and converter circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5466	500	V
		2N5467	700	
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		3	A
I _{CM}	Collector current-peak		5	A
I _B	Base current		1	A
P _D	Total Power Dissipation	T _C =25°C	140	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.48	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.4A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =ratedV _{CB0} ; I _E =0			1.0	mA
I _{CEV}	Collector cut-off current	V _{CE} =ratedV _{CE0} ; V _{BE(off)} =1.5V T _C =125°C			1.0 5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =4V	15		45	
h _{FE-2}	DC current gain	I _C =2A ; V _{CE} =4V	8			
f _T	Transistion frequency	I _C =1A ; V _{CE} =10V;f=1MHz	2.5			MHz

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PACKAGE OUTLINE

